

ABSTRACT OF THE DISCLOSURE

A method for depositing a low dielectric constant film is provided by reacting a gas mixture including one or more linear, oxygen-free organosilicon compounds, one or more oxygen-free hydrocarbon compounds comprising one ring and one or two carbon-carbon double bonds in the ring, and one or more oxidizing gases. Optionally, the low dielectric constant film is post-treated after it is deposited. In one aspect, the post treatment is an electron beam treatment.

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